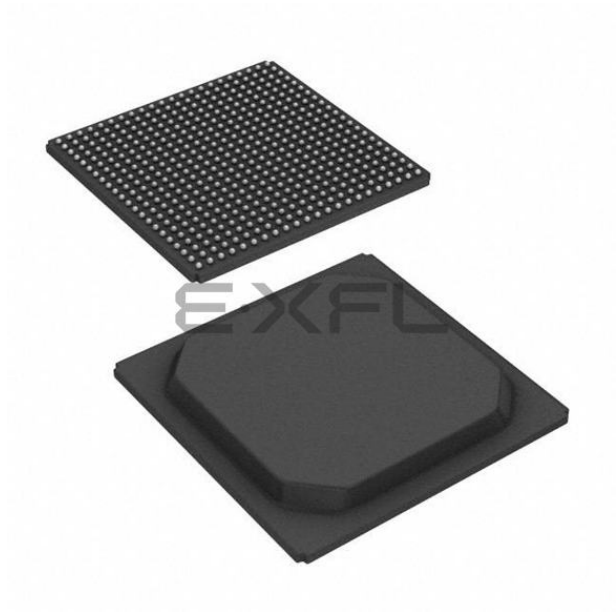

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Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	300000
Total RAM Bits	21094400
Number of I/O	244
Number of Gates	-
Voltage - Supply	0.97V ~ 1.08V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BBGA, FCBGA
Supplier Device Package	484-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/mpf300t-1fcg484i

Contents

Parameter	Symbol	Min	Typ	Max	Unit
Transceiver TX and RX lanes supply at 1.05 V mode (when any lane rate is greater than 10.3125 Gbps)[1]	V_{DDA}	1.02	1.05	1.08	V
Programming and HSIO receiver supply	V_{DD18}	1.71	1.80	1.89	V
FPGA core and FPGA PLL high-voltage supply	V_{DD25}	2.425	2.50	2.575	V
Transceiver PLL high-voltage supply	V_{DDA25}	2.425	2.50	2.575	V
Transceiver reference clock supply –3.3 V nominal	$V_{DD\_XCVR\_CLK}$	3.135	3.3	3.465	V
Transceiver reference clock supply –2.5 V nominal	$V_{DD\_XCVR\_CLK}$	2.375	2.5	2.625	V
Global V_{REF} for transceiver reference clocks[3]	$XCVR_{VREF}$	Ground		$V_{DD\_XCVR\_CLK}$	V
HSIO DC I/O supply. Allowed nominal options: 1.2 V, 1.35 V, 1.5 V, and 1.8 V[4]	V_{DDIx}	1.14	Various	1.89	V
GPIO DC I/O supply. Allowed nominal options: 1.2 V, 1.5 V, 1.8 V, 2.5 V, and 3.3 V[2,4]	V_{DDIx}	1.14	Various	3.465	V
Dedicated I/O DC supply for JTAG and SPI (GPIO Bank 3). Allowed nominal options: 1.8 V, 2.5 V, and 3.3 V	V_{DDI3}	1.71	Various	3.465	V
GPIO auxiliary supply for I/O bank x with V_{DDIx} = 3.3 V nominal[2,4]	V_{DDAUXx}	3.135	3.3	3.465	V
GPIO auxiliary supply for I/O bank x with V_{DDIx} = 2.5 V nominal or lower[2,4]	V_{DDAUXx}	2.375	2.5	2.625	V
Extended commercial temperature range	T_J	0		100	°C
Industrial temperature range	T_J	–40		100	°C
Extended commercial programming temperature range	T_{PRG}	0		100	°C
Industrial programming temperature range	T_{PRG}	–40		100	°C

1. V_{DD} and V_{DDA} can independently operate at 1.0 V or 1.05 V nominal. These supplies are not dynamically adjustable.
2. For GPIO buffers where I/O bank is designated as bank number, if V_{DDIx} is 2.5 V nominal or 3.3 V nominal, V_{DDAUXx} must be connected to the V_{DDIx} supply for that bank. If V_{DDIx} for a given GPIO bank is <2.5 V nominal, V_{DDAUXx} per I/O bank must be powered at 2.5 V nominal.
3. $XCVR_{VREF}$ globally sets the reference voltage of the transceiver's single-ended reference clock input buffers. It is typically near $V_{DD\_XCVR\_CLK}$/2 V but is allowed in the specified range.
4. The power supplies for a given I/O bank x are shown as VDDIx and VDDAUXx.

Table 8 • Maximum Overshoot During Transitions for GPIO

AC (V_{IN}) Overshoot Duration as % at T_J = 100 °C	Condition (V)
100	3.8
100	3.85
100	3.9
100	3.95
70	4
50	4.05
33	4.1
22	4.15
14	4.2
9.8	4.25
6.5	4.3
4.4	4.35
3	4.4
2	4.45
1.4	4.5
0.9	4.55
0.6	4.6

Note: Overshoot level is for V_{DDI} at 3.3 V.

The following table shows the maximum AC input voltage (V_{IN}) undershoot duration for GPIO.

Table 9 • Maximum Undershoot During Transitions for GPIO

AC (V_{IN}) Undershoot Duration as % at T_J = 100 °C	Condition (V)
100	–0.5
100	–0.55
100	–0.6
100	–0.65
100	–0.7
100	–0.75
100	–0.8
100	–0.85
100	–0.9
100	–0.95
100	–1
100	–1.05
100	–1.1
100	–1.15
100	–1.2
69	–1.25
45	–1.3

6.2.2.1 Power-Supply Ramp Times

The following table shows the allowable power-up ramp times. Times shown correspond to the ramp of the supply from 0 V to the minimum recommended voltage as specified in the section Recommended Operating Conditions (see page 6). All supplies must rise and fall monotonically.

Table 10 • Power-Supply Ramp Times

Parameter	Symbol	Min	Max	Unit
FPGA core supply	V_{DD}	0.2	50	ms
Transceiver core supply	V_{DDA}	0.2	50	ms
Must connect to 1.8 V supply	V_{DD18}	0.2	50	ms
Must connect to 2.5 V supply	V_{DD25}	0.2	50	ms
Must connect to 2.5 V supply	V_{DDA25}	0.2	50	ms
HSIO bank I/O power supplies	$V_{DDI[0,1,6,7]}$	0.2	50	ms
GPIO bank I/O power supplies	$V_{DDI[2,4,5]}$	0.2	50	ms
Bank 3 dedicated I/O buffers (GPIO)	V_{DDI3}	0.2	50	ms
GPIO bank auxiliary power supplies	$V_{DDAUX[2,4,5]}$	0.2	50	ms
Transceiver reference clock supply	$V_{DD\_XCVR\_CLK}$	0.2	50	ms
Global V_{REF} for transceiver reference clocks	$XCVR_{VREF}$	0.2	50	ms

Note: For proper operation of programming recovery mode, if a VDD supply brownout occurs during programming, a minimum supply ramp down time for only the VDD supply is recommended to be 10 ms or longer by using a programmable regulator or on-board capacitors.

6.2.2.2 Hot Socketing

The following table lists the hot-socketing DC characteristics over recommended operating conditions.

Table 11 • Hot Socketing DC Characteristics over Recommended Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Current per transceiver Rx input pin (P or N single-ended)[1, 2]	I_{XCVRRX_HS}			±4	mA	V_{DDA} = 0 V
Current per transceiver Tx output pin (P or N single-ended)[3]	I_{XCVRTX_HS}			±10	mA	V_{DDA} = 0 V
Current per transceiver reference clock input pin (P or N single-ended)[4]	$I_{XCVRREF\_HS}$			±1	mA	$V_{DD\_XCVR\_CLK}$ = 0 V
Current per GPIO pin (P or N single-ended)[5]	I_{GPIO_HS}			±1	mA	V_{DDIx} = 0 V
Current per HSIO pin (P or N single-ended)						Hot socketing is not supported in HSIO.

1. Assumes that the device is powered-down, all supplies are grounded, AC-coupled interface, and input pin pairs are driven by a CML driver at the maximum amplitude (1 V pk–pk) that is toggling at any rate with PRBS7 data.
2. Each P and N transceiver input has less than the specified maximum input current.
3. Each P and N transceiver output is connected to a 40 Ω resistor (50 Ω CML termination – 20% tolerance) to the maximum allowed output voltage (V_{DDAmax} + 0.3 V = 1.4 V) through an AC-coupling capacitor with all PolarFire device supplies grounded. This shows the current for a worst-case DC coupled interface. As an AC-coupled interface, the output signal will settle at ground and no hot socket current will be seen.
4. $V_{DD\_XCVR\_CLK}$ is powered down and the device is driven to $–0.3\ V < V_{IN} < V_{DD\_XCVR\_CLK}$.
5. V_{DDIx} is powered down and the device is driven to $–0.3\ V < V_{IN} <$ GPIO V_{DDImax}.

I/O Standard	Bank Type	VICM_RANGE Libero Setting	V_{ICM}[1,3] Min (V)	V_{ICM}[1,3] Typ (V)	V_{ICM}[1,3] Max (V)	V_{ID}[2] Min (V)	V_{ID} Typ (V)	V_{ID} Max (V)
HCSL25[6]	GPIO	Mid (default)	0.6	1.25	2.35	0.1	0.55	1.1
		Low	0.05	0.35	0.8	0.1	0.55	1.1
HCSL18[5]	HSIO	Mid (default)	0.6	1.0	1.65	0.1	0.55	1.1
		Low	0.05	0.4	0.8	0.1	0.55	1.1
BUSLVDSE25	GPIO	Mid (default)	0.6	1.25	2.35	0.05	0.1	V_{DDIn}
		Low	0.05	0.4	0.8	0.05	0.1	V_{DDIn}
MLVDSE25	GPIO	Mid (default)	0.6	1.25	2.35	0.05	0.35	2.4
		Low	0.05	0.4	0.8	0.05	0.35	2.4
LVPECL33	GPIO	Mid (default)	0.6	1.65	2.35	0.05	0.8	2.4
		Low	0.05	0.4	0.8	0.05	0.8	2.4
LVPECLE33	GPIO	Mid (default)	0.6	1.65	2.35	0.05	0.8	2.4
		Low	0.05	0.4	0.8	0.05	0.8	2.4
MIPI25	GPIO	Mid (default)	0.6	1.25	2.35	0.05	0.2	0.3
		Low	0.05	0.2	0.8	0.05	0.2	0.3

1. V_{ICM} is the input common mode.
2. V_{ID} is the input differential voltage.
3. V_{ICM} rules are as follows:
   a. V_{ICM} must be less than V_{DDI} – 0.4 V;
   b. V_{ICM} + V_{ID}/2 must be <V_{DDI} + 0.4 V;
   c. V_{ICM} – V_{ID}/2 must be >VSS – 0.3 V;
   d. Any differential input with V_{ICM} ≤0.6 V requires the low common mode setting in Libero (VICM_RANGE=LOW).
4. VDDI = 1.8 V, VDDAUX = 2.5 V.
5. HSIO receiver only.
6. GPIO receiver only.

Table 15 • Differential DC Output Levels

I/O Standard	Bank Type	V_{OCM}[1] Min (V)	V_{OCM} Typ (V)	V_{OCM} Max (V)	V_{OD}[2] Min (V)	V_{OD}[2] Typ (V)	V_{OD}[2] Max (V)
LVDS33	GPIO		1.2		0.25	0.35	0.45
LVDS25	GPIO		1.2		0.25	0.35	0.45
LCMDS33	GPIO		0.6		0.25	0.35	0.45
LCMDS25	GPIO		0.6		0.25	0.35	0.45
RSDS33	GPIO		1.2		0.17	0.2	0.23
RSDS25	GPIO		1.2		0.17	0.2	0.23
MINILVDS33	GPIO		1.2		0.3	0.4	0.6
MINILVDS25	GPIO		1.2		0.3	0.4	0.6
SUBLVDS33	GPIO		0.9		0.1	0.15	0.3
SUBLVDS25	GPIO		0.9		0.1	0.15	0.3
PPDS33	GPIO		0.8		0.17	0.2	0.23
PPDS25	GPIO		0.8		0.17	0.2	0.23
SLVSE15[3]	GPIO, HSIO		0.2		0.12	0.135	0.15
BUSLVDSE25[3]	GPIO		1.25		0.24	0.262	0.272

I/O Standard	Bank Type	V_{OCM}[1] Min (V)	V_{OCM} Typ (V)	V_{OCM} Max (V)	V_{OD}[2] Min (V)	V_{OD}[2] Typ (V)	V_{OD}[2] Max (V)
MLVDSE25[3]	GPIO		1.25		0.396	0.442	0.453
LVPECLE33[3]	GPIO		1.65		0.664	0.722	0.755
MIPIE25[3]	GPIO		0.25		0.1	0.22	0.3

1. V_{OCM} is the output common mode voltage.
2. V_{OD} is the output differential voltage.
3. Emulated output only.

6.3.3 Complementary Differential DC Input and Output Levels

The following tables list the complementary differential DC I/O levels.

Table 16 • Complementary Differential DC Input Levels

I/O Standard	V_{DDI} Min (V)	V_{DDI} Typ (V)	V_{DDI} Max (V)	V_{ICM}[1,3] Min (V)	V_{ICM}[1,3] Typ (V)	V_{ICM}[1,3] Max (V)	V_{ID}[2] Min (V)	V_{ID} Max (V)
SSTL25I	2.375	2.5	2.625	1.164	1.250	1.339	0.1	
SSTL25II	2.375	2.5	2.625	1.164	1.250	1.339	0.1	
SSTL18I	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
SSTL18II	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
SSTL15I	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
SSTL15II	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
SSTL135I	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
SSTL135II	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
HSTL15I	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
HSTL15II	1.425	1.5	1.575	0.698	0.750	0.803	0.1	
HSTL135I	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
HSTL135II	1.283	1.35	1.418	0.629	0.675	0.723	0.1	
HSTL12I	1.14	1.2	1.26	0.559	0.600	0.643	0.1	
HSUL18I	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
HSUL18II	1.71	1.8	1.89	0.838	0.900	0.964	0.1	
HSUL12I	1.14	1.2	1.26	0.559	0.600	0.643	0.1	
POD12I	1.14	1.2	1.26	0.787	0.840	0.895	0.1	
POD12II	1.14	1.2	1.26	0.787	0.840	0.895	0.1	

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage.
3. V_{ICM} rules are as follows:
   a. V_{ICM} must be less than V_{DDI} -0.4V;
   b. $V_{ICM} + V_{ID}/2$ must be $<V_{DDI} + 0.4$ V;
   c. $V_{ICM} – V_{ID}/2$ must be >VSS – 0.3 V.

Figure 1 • Output Delay Measurement—Single-Ended Test Setup

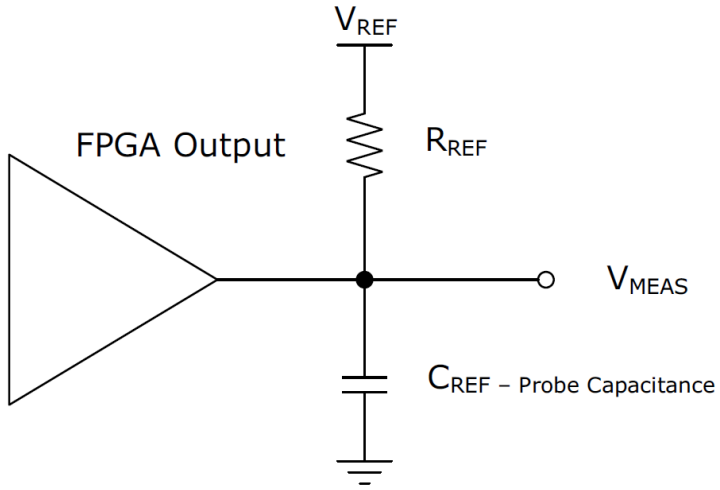
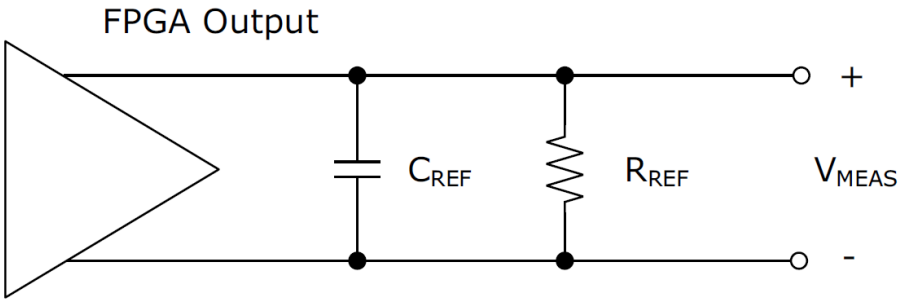


Figure 2 • Output Delay Measurement—Differential Test Setup



7.1.3 Input Buffer Speed

The following tables provide information about input buffer speed.

Table 24 • HSIO Maximum Input Buffer Speed

Standard	STD	–1	Unit
LVDS18	1250	1250	Mbps
RSDS18	800	800	Mbps
MINILVDS18	800	800	Mbps
SUBLVDS18	800	800	Mbps
PPDS18	800	800	Mbps
SLVS18	800	800	Mbps
SSTL18I	800	1066	Mbps
SSTL18II	800	1066	Mbps
SSTL15I	1066	1333	Mbps
SSTL15II	1066	1333	Mbps
SSTL135I	1066	1333	Mbps
SSTL135II	1066	1333	Mbps

Standard	STD	–1	Unit
HSTL15I	900	1100	Mbps
HSTL15II	900	1100	Mbps
HSTL135I	1066	1066	Mbps
HSTL135II	1066	1066	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
HSUL12	1066	1333	Mbps
HSTL12	1066	1266	Mbps
POD12I	1333	1600	Mbps
POD12II	1333	1600	Mbps
LVCMOS18 (12 mA)	500	500	Mbps
LVCMOS15 (10 mA)	500	500	Mbps
LVCMOS12 (8 mA)	300	300	Mbps

1. Performance is achieved with V_{ID} ≥200 mV.

Table 25 • GPIO Maximum Input Buffer Speed

Standard	STD	–1	Unit
LVDS25/LVDS33/LCMDS25/LCMDS33	1250	1600	Mbps
RSDS25/RSDS33	800	800	Mbps
MINILVDS25/MINILVDS33	800	800	Mbps
SUBLVDS25/SUBLVDS33	800	800	Mbps
PPDS25/PPDS33	800	800	Mbps
SLVS25/SLVS33	800	800	Mbps
SLVSE15	800	800	Mbps
HCSL25/HCSL33	800	800	Mbps
BUSLVDSE25	800	800	Mbps
MLVDSE25	800	800	Mbps
LVPECL33	800	800	Mbps
SSTL25I	800	800	Mbps
SSTL25II	800	800	Mbps
SSTL18I	800	800	Mbps
SSTL18II	800	800	Mbps
SSTL15I	800	1066	Mbps
SSTL15II	800	1066	Mbps
HSTL15I	800	900	Mbps
HSTL15II	800	900	Mbps
HSUL18I	400	400	Mbps
HSUL18II	400	400	Mbps
PCI	500	500	Mbps
LVTTL33 (20 mA)	500	500	Mbps
LVCMOS33 (20 mA)	500	500	Mbps
LVCMOS25 (16 mA)	500	500	Mbps

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Clock-to-Data Condition
FMAX 8:1	RX_DDRX_BL_C	Rx DDR digital mode							MHz	From a HS_IO_CLK clock source, centered

Table 32 • I/O Digital Transmit Single-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Forwarded Clock-to-Data Skew
Output FMAX	TX_SDR_G_A	Tx SDR							MHz	From a global clock source, aligned[1]
	TX_SDR_G_C	Tx SDR							MHz	From a global clock source, centered[1]

1. A centered clock-to-data interface can be created with a negedge launch of the data.

Table 33 • I/O Digital Transmit Double-Data Rate Switching Characteristics

Parameter	Interface Name	Topology	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit	Forwarded Clock-to-Data Skew
Output FMAX	TX_DDR_G_A	Tx DDR			335			335	MHz	From a global clock source, aligned
	TX_DDR_G_C	Tx DDR			335			335	MHz	From a global clock source, centered
	TX_DDR_L_A	Tx DDR			250			250	MHz	From a lane clock source, aligned
	TX_DDR_L_C	Tx DDR			250			250	MHz	From a lane clock source, centered
Output FMAX 2:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
Output FMAX 4:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned
Output FMAX 8:1	TX_DDRX_B_A	Tx DDR digital mode							MHz	From a HS_IO_CLK clock source, aligned

Parameter	Symbol	Min	Typ	Max	Unit
Operating current (V_{DD18})	RC_{SCVPP}			0.1	µA
Operating current (V_{DD})	RC_{SCVDD}			60.7	µA

7.3.2 SRAM Blocks

The following tables describe the LSRAM blocks' performance.

Table 43 • LSRAM Performance Industrial Temperature Range (–40 °C to 100 °C)

Parameter	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit	Condition
Operating frequency	343	428	343	428	MHz	Two-port, all supported widths, pipelined, simple-write, and write-feed-through
	309	428	309	428	MHz	Two-port, all supported widths, non-pipelined, simple-write, and write-feed-through
	343	428	343	428	MHz	Dual-port, all supported widths, pipelined, simple-write, and write-feed-through
	309	428	309	428	MHz	Dual-port, all supported widths, non-pipelined, simple-write, and write-feed-through
	343	428	343	428	MHz	Two-port pipelined ECC mode, pipelined, simple-write, and write-feed-through
	279	295	279	295	MHz	Two-port non-pipelined ECC mode, pipelined, simple-write, and write-feed-through
	343	428	343	428	MHz	Two-port pipelined ECC mode, non-pipelined, simple-write, and write-feed-through
	196	285	196	285	MHz	Two-port non-pipelined ECC mode, non-pipelined, simple-write, and write-feed-through
	274	285	274	285	MHz	Two-port, all supported widths, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port, all supported widths, non-pipelined, and read-before-write
	274	285	274	285	MHz	Dual-port, all supported widths, pipelined, and read-before-write
	274	285	274	285	MHz	Dual-port, all supported widths, non-pipelined, and read-before-write
	274	285	274	285	MHz	Two-port pipelined ECC mode, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port non-pipelined ECC mode, pipelined, and read-before-write
	274	285	274	285	MHz	Two-port pipelined ECC mode, non-pipelined, and read-before-write
	193	285	193	285	MHz	Two-port non-pipelined ECC mode, non-pipelined, and read-before-write

Table 44 • µSRAM Performance

Parameter	Symbol	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit	Condition
Operating frequency	F_{MAX}	400	415	450	480	MHz	Write-port
Read access time	Tac		2		2	ns	Read-port

Table 45 • µPROM Performance

Parameter	Symbol	V_{DD} = 1.0 V – STD	V_{DD} = 1.0 V – 1	V_{DD} = 1.05 V – STD	V_{DD} = 1.05 V – 1	Unit
Read access time	Tac	10	10	10	10	ns

7.4 Transceiver Switching Characteristics

This section describes transceiver switching characteristics.

7.4.1 Transceiver Performance

The following table describes transceiver performance.

Table 46 • PolarFire Transceiver and TXPLL Performance

Parameter	Symbol	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit
Tx data rate[1,2]	F_{TXRate}	0.25		10.3125	0.25		12.7	Gbps
Tx OOB (serializer bypass) data rate	$F_{TXRateOOB}$	DC		1.5	DC		1.5	Gbps
Rx data rate when AC coupled[2]	$F_{RxRateAC}$	0.25		10.3125	0.25		12.7	Gbps
Rx data rate when DC coupled	$F_{RxRateDC}$	0.25		3.2	0.25		3.2	Gbps
Rx OOB (deserializer bypass) data rate	$F_{TXRateOOB}$	DC		1.25	DC		1.25	Gbps
TXPLL output frequency[3]	F_{TXPLL}	1.6		6.35	1.6		6.35	GHz
Rx CDR mode	F_{RXCDR}	0.25		10.3125	0.25		10.3125	Gbps
Rx DFE mode[2]	F_{RXDFE}	3.0		10.3125	3.0		12.7	Gbps
Rx Eye Monitor mode[2]	$F_{RXEyeMon}$	3.0		10.3125	3.0		12.7	Gbps

1. The reference clock is required to be a minimum of 75 MHz for data rates of 10 Gbps and above.
2. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6).
3. The Tx PLL rate is between 0.5x to 5.5x the Tx data rate. The Tx data rate depends on per XCVR lane Tx post-divider settings.

7.4.2 Transceiver Reference Clock Performance

The following table describes performance of the transceiver reference clock.

Table 47 • PolarFire Transceiver Reference Clock AC Requirements

Parameter	Symbol	STD Min	STD Typ	STD Max	–1 Min	–1 Typ	–1 Max	Unit
Reference clock input rate[1, 2]	$F_{TXREFCLK}$	20		800	20		800	MHz

7.5.7 CPRI

The following table describes CPRI.

Table 66 • CPRI

	Data Rate	Min	Max	Unit
Total transmit jitter	0.6144 Gbps			UI
	1.2288 Gbps			UI
	2.4576 Gbps			UI
	3.0720 Gbps			UI
	4.9152 Gbps			UI
	6.1440 Gbps			UI
	9.8304 Gbps			UI
	10.1376 Gbps			UI
	12.16512 Gbps [1]			UI
Receive jitter tolerance	0.6144 Gbps			UI
	1.2288 Gbps			UI
	2.4576 Gbps			UI
	3.0720 Gbps			UI
	4.9152 Gbps			UI
	6.1440 Gbps			UI
	9.8304 Gbps			UI
	10.1376 Gbps			UI
	12.16512 Gbps [1]			UI

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05 V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6).

7.5.8 JESD204B

The following table describes JESD204B.

Table 67 • JESD204B

Parameter	Data Rate	Min	Max	Unit
Total transmit jitter	3.125 Gbps		0.35	UI
	6.25 Gbps		0.3	UI
	12.5 Gbps[1]			UI
Receive jitter tolerance	3.125 Gbps	0.56		UI
	6.25 Gbps	0.6		UI
	12.5 Gbps[1]			UI

1. For data rates greater than 10.3125 Gbps, VDDA must be set to 1.05V mode. See supply tolerance in the section Recommended Operating Conditions (see page 6).

7.6 Non-Volatile Characteristics

The following section describes non-volatile characteristics.

Parameter	Typ	Max	Unit	Conditions
Time to destroy data in non-volatile memory (recoverable)[1, 3]			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non-recoverable)[1, 4]			ms	One iteration of scrubbing
Time to scrub the fabric data[1]			s	Full scrubbing
Time to scrub the pNVM data (like new)[1, 2]			s	Full scrubbing
Time to scrub the pNVM data (recoverable)[1, 3]			s	Full scrubbing
Time to scrub the fabric data PNVM data (non-recoverable)[1, 4]			s	Full scrubbing
Time to verify[5]			s	

1. Total completion time after interning zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 79 • Zeroization Times for MPF300T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data[1]			ms	Data erased
Time to destroy data in non-volatile memory (like new)[1, 2]			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable)[1, 3]			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (non- recoverable)[1, 4]			ms	One iteration of scrubbing
Time to scrub the fabric data[1]			s	Full scrubbing
Time to scrub the pNVM data (like new)[1, 2]			s	Full scrubbing
Time to scrub the pNVM data (recoverable)[1, 3]			s	Full scrubbing
Time to scrub the fabric data pNVM data (non-recoverable)[1, 4]			s	Full scrubbing
Time to verify[5]			s	

1. Total completion time after interning zeroization.
2. Like new mode—zeroizes user design security setting and sNVM content.
3. Recoverable mode—zeroizes user design security setting, sNVM and factory keys.
4. Non-recoverable mode—zeroizes user design security setting, sNVM and factory keys, and factory data required for programming.
5. Time to verify after scrubbing completes.

Table 80 • Zeroization Times for MPF500T, TL, TS, and TLS Devices

Parameter	Typ	Max	Unit	Conditions
Time to enter zeroization			ms	Zip flag set
Time to destroy the fabric data[1]			ms	Data erased
Time to destroy data in non-volatile memory (like new)[1, 2]			ms	One iteration of scrubbing
Time to destroy data in non-volatile memory (recoverable)[1, 3]			ms	One iteration of scrubbing

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Authenticated text read		113.25	114.02	118.5	µs	
Authenticated and decrypted text read		159.59	160.53	166.5	µs	

Notes:

- Page size= 252 bytes (non-authenticated), 236 bytes (authenticated).
- Only page reads and writes allowed.
- T_{PUF_OVHD} is an additional time that occurs on the first R/W, after cold or warm boot, to sNVM using authenticated or authenticated and encrypted text.

7.6.10 Secure NVM Programming Cycles

The following table describes secure NVM programming cycles.

Table 86 • sNVM Programming Cycles vs. Retention Characteristics

Programming Temperature	Programming Cycles per Page, Max	Programming Cycles per Block, Max	Retention Years
–40 °C to 100 °C	10,000	100,000	20
–40 °C to 85 °C	10,000	100,000	20
–40 °C to 55 °C	10,000	100,000	20

Note: Page size = 128 bytes. Block size = 56 KBytes.

7.7 System Services

This section describes system switching and throughput characteristics.

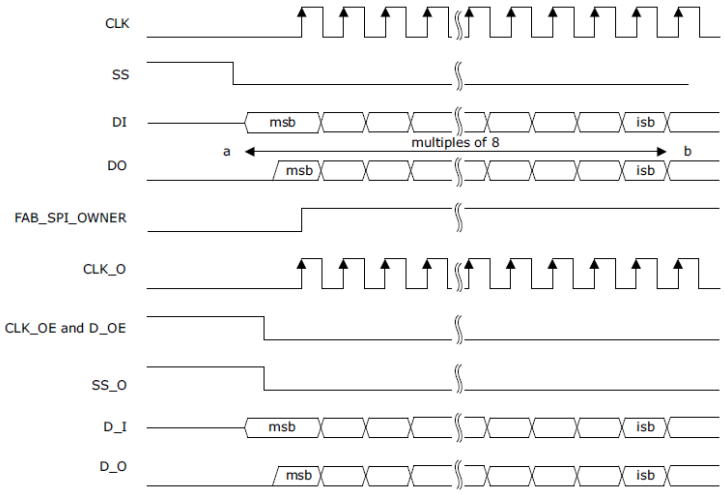
7.7.1 System Services Throughput Characteristics

The following table describes system services throughput characteristics.

Table 87 • System Services Throughput Characteristics

Parameter	Symbol	Service ID	Typ	Max	Unit	Conditions
Serial number	T_{Serial}	00H	65	67	µs	
User code	T_{User}	01H	0.8	1.05	µs	
Design information	T_{Design}	02H	2.4	2.7	µs	
Device certificate	T_{Cert}	03H	255	271	ms	
Read digests	T_{digest_read}	04H	201	215	µs	
Query security locks	T_{sec_Query}	05H	15	17	µs	
Read debug information	T_{Rd_debug}	06H	34	38	µs	
Reserved		07H–0FH				
Secure NVM write plain text	$T_{SNVM\_Wr\_Plain}$	10H				Note 1
Secure NVM write authenticated plain text	$T_{SNVM\_Wr\_Auth}$	11H				Note 1
Secure NVM write authenticated cipher text	$T_{SNVM\_Wr\_Cipher}$	12H				Note 1
Reserved		13H–17H				

Figure 4 • USPI Switching Characteristics



7.8.4 Tamper Detectors

The following section describes tamper detectors.

Table 91 • ADC Conversion Rate

Parameter	Description	Min	Typ[1]	Max
T_{CONV1}	Time from enable changing from zero to non-zero value to first conversion completes. Minimum value applies when POWEROFF = 0.	420 µs		470 µs
T_{CONVN}	Time between subsequent channel conversions.		480 µs	
T_{SETUP}	Data channel and output to valid asserted. Data is held until next conversion completes, that is >480 µs.	0 ns		
T_{VALID}[2]	Width of the valid pulse.	1.625 µs		2 µs
T_{RATE}	Time from start of first set of conversions to the start of the next set. Can be considered as the conversion rate. Is set by the conversion rate parameter.	480 µs	Rate × 32 µs	8128 µs

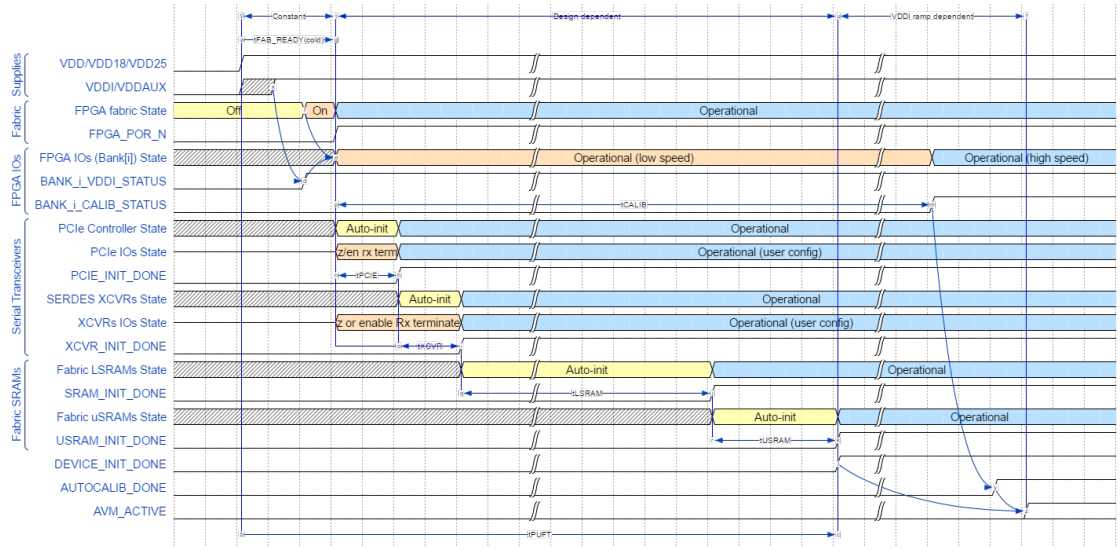
1. Min, typ, and max refer to variation due to functional configuration and the raw TVS value. The actual internal correction time will vary based on the raw TVS value.
2. The pulse width varies depending on the time taken to complete the internal calibration multiplication, this can be up to 375 ns.

Note: Once the TVS block is active, the enable signal is sampled 25 ns before the falling edge of valid. The next enabled channel in the sequence 0-1-2-3 is started; that is, if channel 0 has just completed and only channels 0 and 3 are enabled, the next channel will be 3. When all the enabled channels in the sequence 0-1-2-3 are completed, the TVS waits for the conversion rate timer to expire. The enable signal may be changed at any time if it changes to 4'b0000 while valid is asserted (and 25 ns before valid is de-asserted), then no further conversions will be started.

Table 92 • Temperature and Voltage Sensor Electrical Characteristics

Parameter	Min	Typ	Max	Unit	Condition
Temperature sensing range	–40		125	°C	
Temperature sensing accuracy	–10		10	°C	

Figure 5 • Cold Reset Timing



Notes:

- The previous diagram showsthe case where VDDI/VDDAUX of I/O banks are powered either before or sufficiently soon after VDD/VDD18/VDD25 that the I/O bank enable time is measured from the assertion time of VDD/VDD18/VDD25 (that is, the PUFT specification). If VDDI/VDDAUX of I/O banks are powered sufficiently after VDD/VDD18/VDD25, then the I/O bank enable time is measured from the assertion of VDDI/VDDAUX and is not specified by the PUFT specification. In this case, I/O operation is indicated by the assertion of BANK_i_VDDI_STATUS, rather than being measured relative to FABRIC_POR_N negation.
- AUTOCALIB_DONE assertion indicates the completion of calibration for any I/O banks specified by the user for auto-calibration. AUTOCALIB_DONE asserts independently of DEVICE_INIT_DONE. It may assert before or after DEVICE_INIT_DONE and is determined by the following:
  - How long after VDD/VDD18/VDD25 that VDDI/VDDAUX are powered on. Note that if any of the user-specified I/O banks are not powered on within the auto-calibration timeout window, then AUTOCALIB_DONE doesn't assert until after this timeout.
  - The specified ramp times of VDDI of each I/O bank designated for auto-calibration.
  - How much auto-initialization is to be performed for the PCIe, SERDES transceivers, and fabric LSRAMs.
- If any of the I/O banks specified for auto-calibration do not have their VDDI/VDDAUX powered on within the auto-calibration timeout window, then it will be approximately auto-calibrated whenever VDDI/VDDAUX is subsequently powered on. To obtain an accurate calibration however, on such IO banks, it is necessary to initiate a re-calibration (using CALIB_START from fabric).
- AVM_ACTIVE only asserts if avionics mode is being used. It is asserted when the later of DEVICE_INIT_DONE or AUTOCALIB_DONE assert.

7.9.2 Warm Reset Initialization Sequence

The following warm reset timing diagram shows the initialization sequencing of the device when either DEVRST_N or TAMPER_RESET_DEVICE signals are asserted.

7.11 User Crypto

The following section describes user crypto.

7.11.1 TeraFire 5200B Switching Characteristics

The following table describes TeraFire 5200B switching characteristics.

Table 112 • TeraFire F5200B Switching Characteristics

Parameter	Symbol	VDD = 1.0 V STD	VDD = 1.0 V – 1	VDD = 1.05 V STD	VDD = 1.05 V – 1	Unit	Condition
Operating frequency	F_{MAX}	189		189		MHz	–40 °C to 100 °C

7.11.2 TeraFire 5200B Throughput Characteristics

The following tables for each algorithm describe the TeraFire 5200B throughput characteristics.

Note: Throughput cycle count collected with Athena TeraFire Core and RISCV running at 100 MHz.

Table 113 • AES

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-ECB-128 encrypt[1]	128	515	1095
	64K	50157	933
AES-ECB-128 decrypt[1]	128	557	1760
	64K	48385	1524
AES-ECB-256 encrypt[1]	128	531	1203
	64K	58349	1203
AES-ECB-256 decrypt[1]	128	589	1676
	64K	56673	1671
AES-CBC-256 encrypt[1]	128	576	1169
	64K	52547	1169
AES-CBC-256 decrypt[1]	128	585	1744
	64K	48565	1652
AES-GCM-128 encrypt[1], 128-bit tag, (full message encrypted/authenticated)	128	1925	2740
	64K	60070	2158
AES-GCM-256 encrypt[1], 128-bit tag, (full message encrypted/authenticated)	128	1973	2268
	64K	60102	2151

1. With DPA counter measures.

Table 114 • GMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-GCM-256[1], 128-bit tag, (message is only authenticated)	128	1863	2211
	64K	49707	2128

1. With DPA counter measures.

Table 115 • HMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
HMAC-SHA-256[1], 256-bit key	512	7477	2361
	64K	88367	2099
HMAC-SHA-384[1], 384-bit key	1024	13049	2257
	64K	106103	2153

1. With DPA counter measures.

Table 116 • CMAC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
AES-CMAC-256[1] (message is only authenticated)	128	446	9058
	64K	45494	111053

1. With DPA counter measures.

Table 117 • KEY TREE

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
128-bit nonce + 8-bit optype		102457	2751
256-bit nonce + 8-bit optype		103218	2089

Table 118 • SHA

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
SHA-1[1]	512	2386	1579
	64K	77576	990
SHA-256[1]	512	2516	884
	64K	84752	938
SHA-384[1]	1024	4154	884
	64K	100222	938
SHA-512[1]	1024	4154	881
	64K	100222	935

1. With DPA counter measures.

Table 119 • ECC

Modes	Message Size (bits)	Athena TeraFire Crypto Core Clock-Cycles	CAL Delay In CPU Clock-Cycles
ECDSA SigGen, P-384/SHA-384[1]	1024	12528912	6944
	8K	12540448	5643
ECDSA SigGen, P-384/SHA-384	1024	5502928	6155

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